

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

MCH6662 —

General-Purpose Switching Device Applications

Features

- ON-resistance Nch: $RDS(on)1=120m\Omega(typ.)$
- · 1.8V drive
- · Halogen free compliance
- · Protection diode in

Specifications

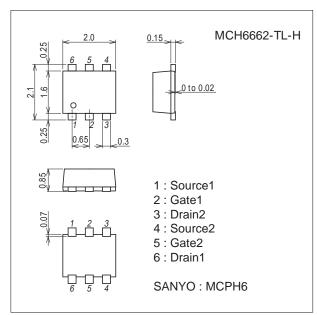
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		2.0	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	8.0	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	0.8	W
Channel Temperature	Tch		150	C
Storage Temperature	Tstg		-55 to +150	C

N-Channel Silicon MOSFET

Package Dimensions

unit : mm (typ) 7022A-006



Product & Package Information

• Package : MCPH6

• JEITA, JEDEC : SC-88, SC-70-6, SOT-363

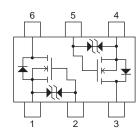
• Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL

Marking



Electrical Connection

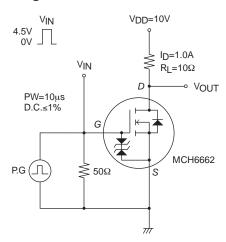


MCH6662

Electrical Characteristics at Ta=25°C

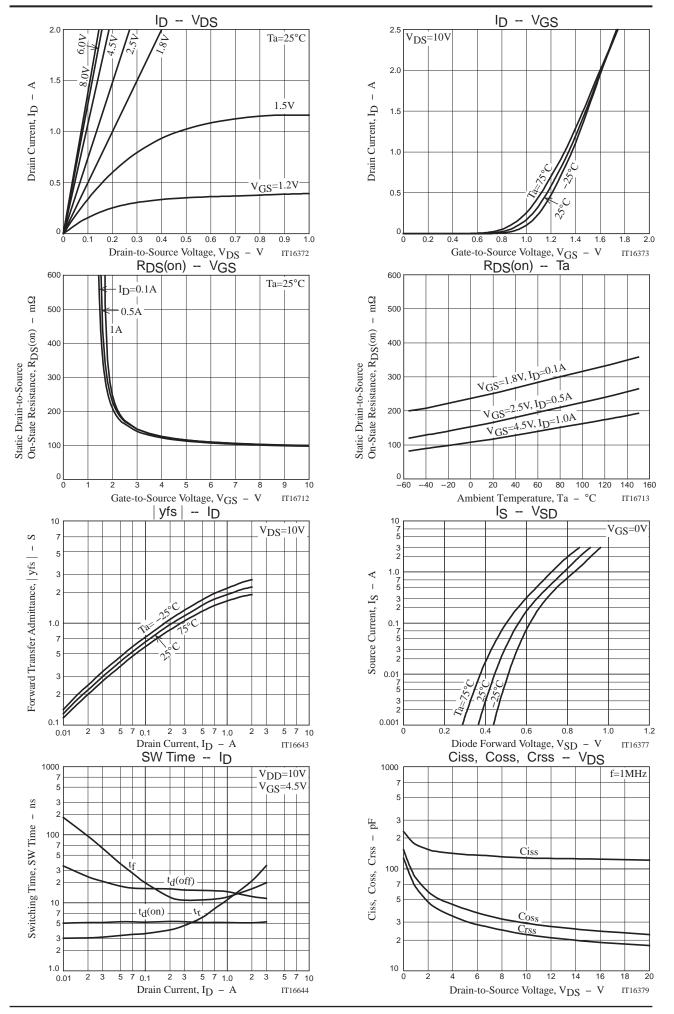
Parameter	Symbol	Conditions	Ratings			Linit	
Farameter	Syllibol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1A		1.9		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =1.0A, V _G S=4.5V			160	mΩ	
	R _{DS} (on)2	I _D =0.5A, V _G S=2.5V		170	240	mΩ	
	R _{DS} (on)3	I _D =0.1A, V _G S=1.8V		255	380	mΩ	
Input Capacitance	Ciss			128		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		28		pF	
Reverse Transfer Capacitance	Crss			21		pF	
Turn-ON Delay Time	t _d (on)			5.1		ns	
Rise Time	t _r	Considered Total Circuit		11		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		14.5		ns	
Fall Time	tf			12		ns	
Total Gate Charge	Qg			1.8		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		0.3		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		0.55		nC	
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0V		0.85	1.2	V	

Switching Time Test Circuit

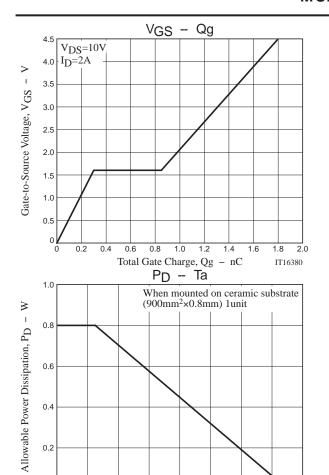


Ordering Information

Device	Package	Shipping	memo	
MCH6662-TL-H	CH6662-TL-H MCPH6		Pb Free and Halogen Free	



MCH6662



ol

0

20

60

80

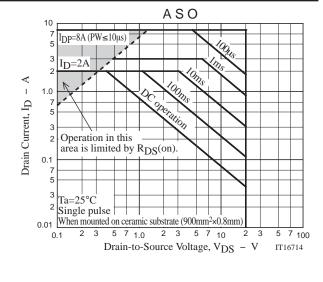
Ambient Temperature, Ta - °C

100

140

160

IT16715

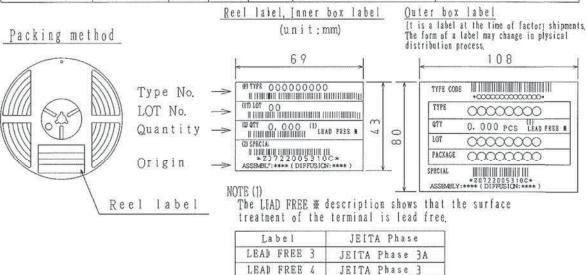


Embossed Taping Specification

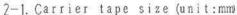
MCH6662-TL-H

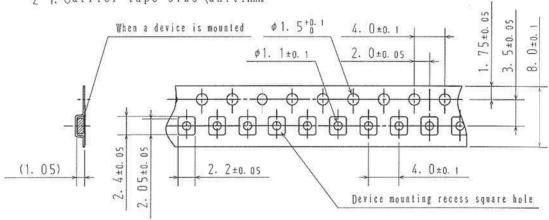
1. Packing Format

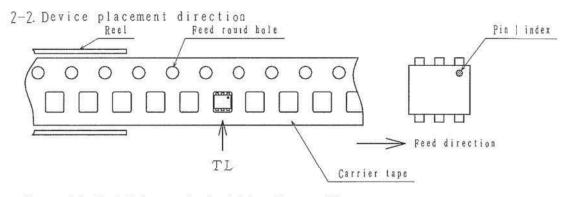
Package Name Carrier Tape Type	Carrier Tape	Maximum Number of devices contained (ecs)			Packing format		
	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
мсрн6	MCP4	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210	



2. Taping configuration





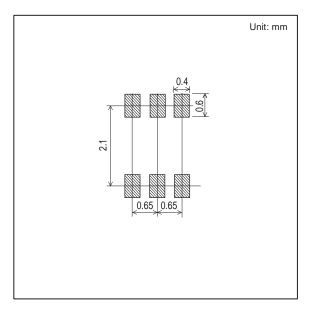


Those with pin 1 index on the feed hole side ·····TL

Outline Drawing

MCH6662-TL-H

Land Pattern Example



Note on usage: Since the MCH6662 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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